

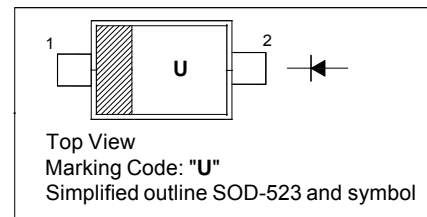
SILICON BAND SWITCHING DIODE

Applications

for band switching in VHF television tuners
and surface mount band switching circuits

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	35	V
Forward Current	I_F	100	mA
Junction Temperature	T_J	150	$^\circ\text{C}$
Operating Temperature Range	T_{op}	- 55 to + 125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

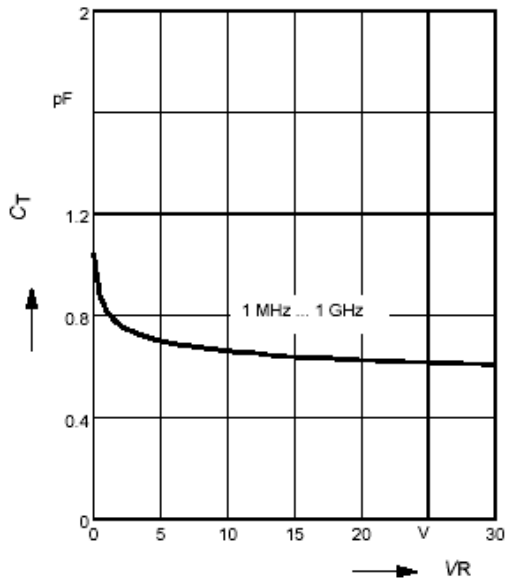
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Current at $V_R = 20\text{ V}$	I_R	-	-	20	nA
Forward Voltage at $I_F = 100\text{ mA}$	V_F	-	-	1	V
Diode Capacitance at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$ at $V_R = 3\text{ V}$, $f = 1\text{ MHz}$ at $V_R = 0\text{ V}$, $f = 100\text{ MHz}$	C_T	0.65 0.6 -	- - 1	1.4 1.1 -	pF
Forward Resistance at $I_F = 3\text{ mA}$, $f = 100\text{ MHz}$ at $I_F = 10\text{ mA}$, $f = 100\text{ MHz}$	r_f	- -	- -	0.7 0.5	Ω
Series Inductance	L_s	-	0.6	-	nH

BA892WT

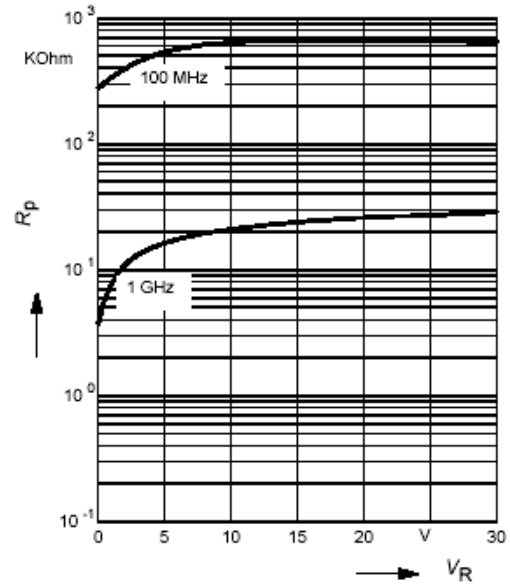
Diode capacitance $C_T = f(V_R)$

$f =$ Parameter



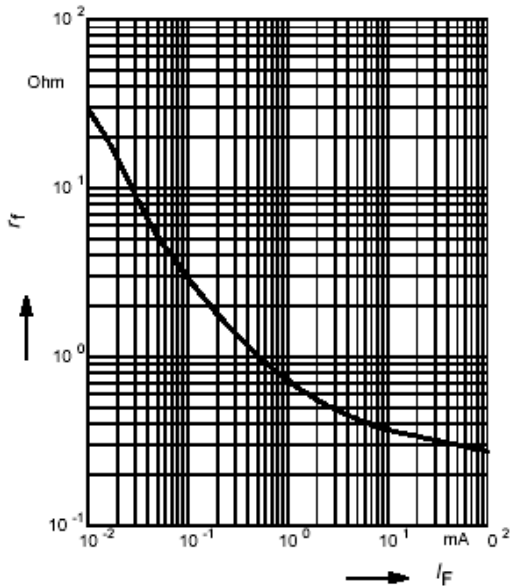
Reverse parallel resistance $R_P = f(V_R)$

$f =$ Parameter



Forward resistance $r_f = f(I_F)$

$f = 100\text{MHz}$



Forward current $I_F = f(V_F)$

$T_A =$ Parameter

